NTGD1100L

Power MOSFET

8 V, ±3.3 A, Load Switch with Level−Shift, P−Channel, TSOP−6

The NTGD1100L integrates a P and N−Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The P−Channel device is specifically designed as a load switch using ON Semiconductor state−of−the−art trench technology. The N−Channel, with an external resistor (R1), functions as a level−shift to drive the P−Channel. The N−Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The NTGD1100L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 3.3 A with 8.0 V applied to both V_{IN} and $V_{ON/OFF}$

Features

- Extremely Low $R_{DS(on)}$ Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- V_{IN} Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- ESD Rating of 2000 V
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating			Symbol	Value	Unit
Input Voltage (V_{DSS}, P−Ch)			V_{IN}	8.0	V
ON/OFF Voltage (V_{GS}, N−Ch)			$V_{ON/OFF}$	8.0	V
Continuous Load Current (Note 1)	Steady State	T_A = 25°C	I_L	±3.3	A
		T_A = 85°C		±2.4	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	0.83	W
		T_A = 85°C		0.43	
Pulsed Load Current	tp = 10 μs		I_{LM}	±10	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.0	A
ESD Rating, MIL−STD−883D HBM (100 pF, 1.5 kΩ)			ESD	2.0	kV
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

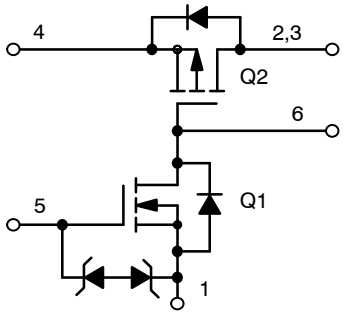
1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ON Semiconductor®

http://onsemi.com

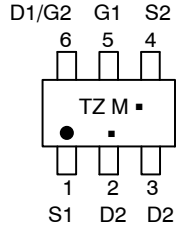
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
8.0 V	40 mΩ @ −4.5 V	±3.3 A
	55 mΩ @ −2.5 V	
	80 mΩ @ −1.8 V	

SIMPLIFIED SCHEMATIC



MARKING DIAGRAM & PIN ASSIGNMENT

TSOP−6
CASE 318G
STYLE 11



TZ = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTGD1100LT1G	TSOP−6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Rating	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 2)	$R_{\mu JA}$	150	°C/W
Junction−to−Foot − Steady State (Note 2)	$R_{\mu JF}$	50	

2. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Q2 Drain−to−Source Breakdown Voltage	V_{IN}	V_{GS2} = 0 V, I_{D2} = 250 μA		8.0			V
Forward Leakage Current	I_{FL}	V_{GS2} = 0 V, V_{DS2} = 8.0 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Q1 Gate−to−Source Leakage Current	I_{GSS}	V_{DS1} = 0 V, V_{GS1} = ±8.0 V				±100	nA
Q1 Diode Forward On−Voltage	V_{SD}	I_S = −1.0 A, V_{GS1} = 0 V			−0.7	−1.0	V
ON CHARACTERISTICS							
Voltage ON/OFF	$V_{ON/OFF}$			1.5		8.0	V
Q1 Gate Threshold Voltage	V_{GS1}	V_{GS1} = V_{DS1}, I_D = 50 μA		0.6		1.2	V
Input Voltage	V_{IN}	V_{GS2} = V_{DS2}, I_D = 250 μA		1.8		8.0	V
Q2 Drain−to−Source On Resistance	$R_{DS(on)}$	$V_{ON/OFF}$ = 1.5 V, I_L = 1.0 A	V_{IN} = 4.5 V		40	55	mΩ
			V_{IN} = 2.5 V		55	70	
			V_{IN} = 1.8 V		80	140	
Load Current	I_L	V_{DROP} ≤ 0.2 V, V_{IN} = 5.0 V, $V_{ON/OFF}$ = 1.5 V		1.0			A
		V_{DROP} ≤ 0.2 V, V_{IN} = 2.5 V, $V_{ON/OFF}$ = 1.5 V		1.0			
		V_{DROP} ≤ 0.2 V, V_{IN} = 1.8 V, $V_{ON/OFF}$ = 1.5 V		1.0			

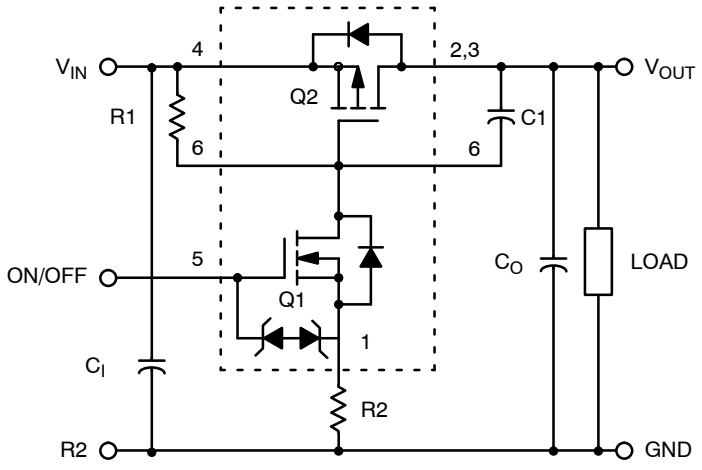


Figure 1. Load Switch Application

Components	Description	Values
R1	Pullup Resistor	Typical 10 kΩ to 1.0 MΩ
R2	Optional Slew−Rate Control	Typical 0 to 100 kΩ
C0	Output Capacitance	Usually < 1.0 μF
C1	Optional In−Rush Current Control	Typical ≤ 1000 pF

TYPICAL CHARACTERISTICS

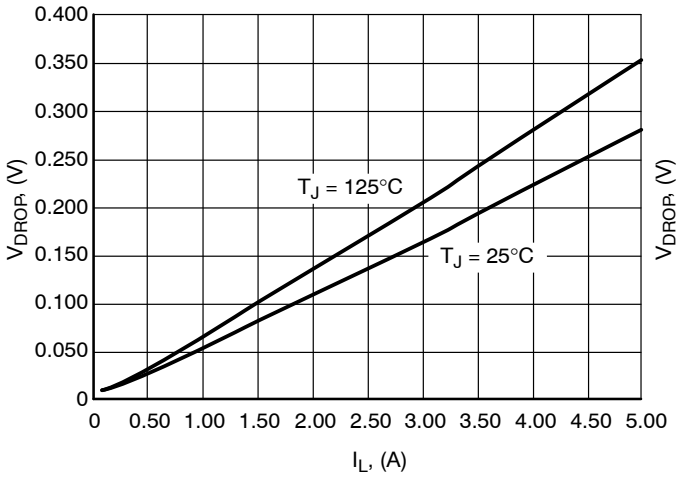


Figure 2. V_{DROP} vs. I_L @ V_{IN} = 2.5 V

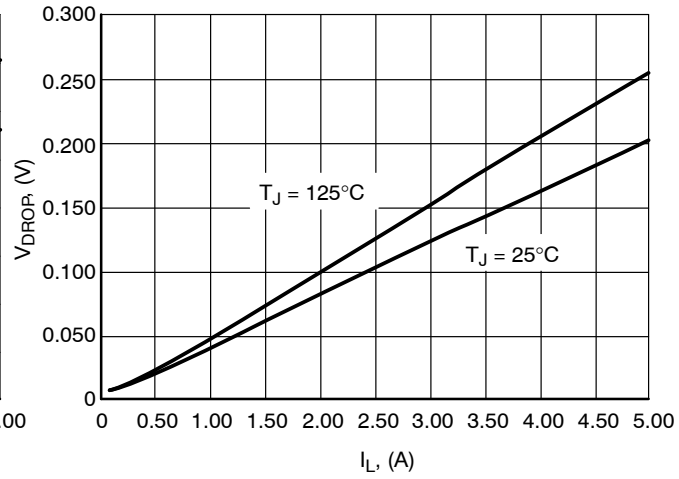


Figure 3. V_{DROP} vs. I_L @ V_{IN} = 4.5 V

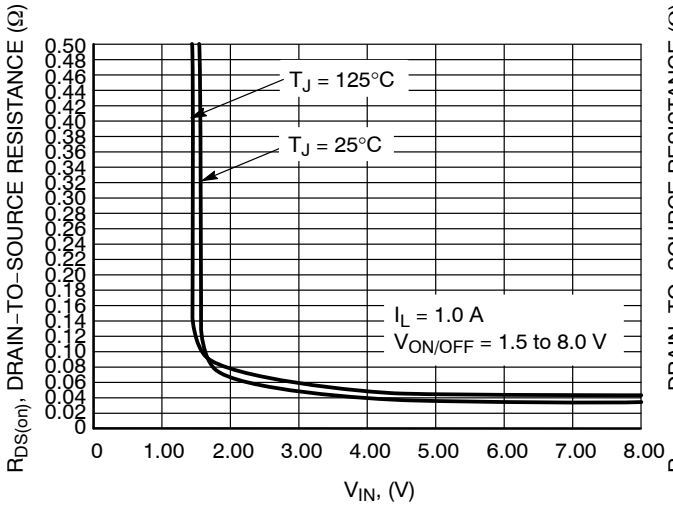


Figure 4. On Resistance vs. Input Voltage

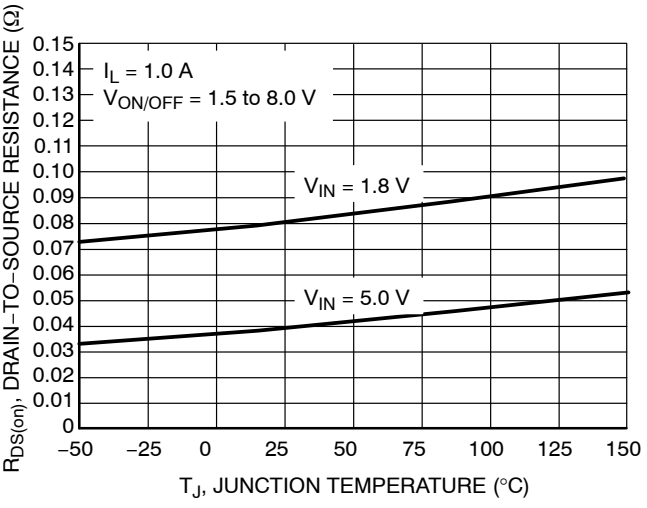


Figure 5. On Resistance Variation with Temperature

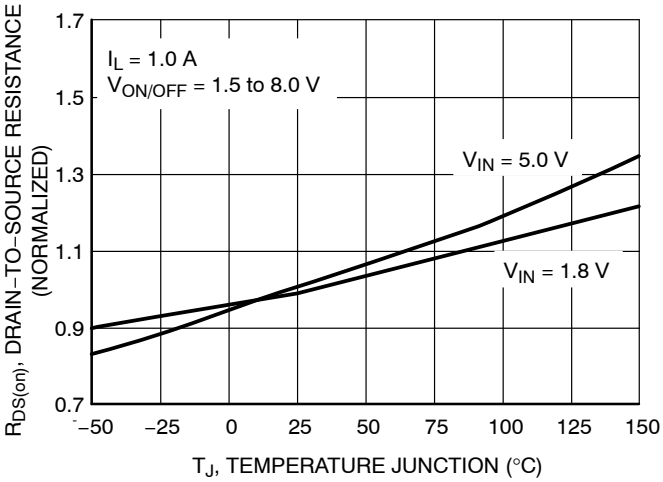


Figure 6. Normalized On Resistance Variation with Temperature

TYPICAL CHARACTERISTICS

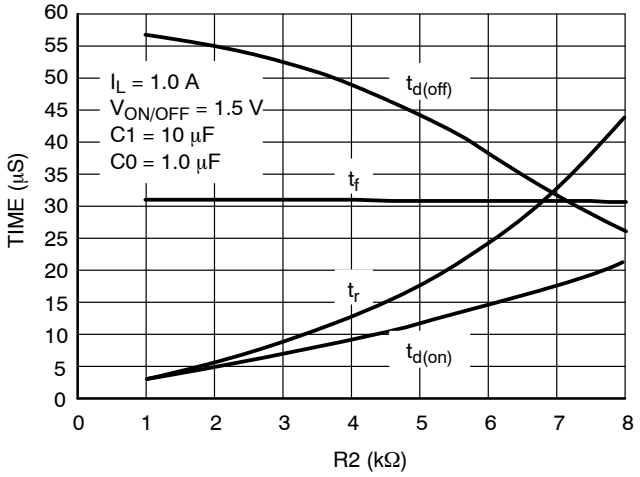


Figure 7. Switching Variation R2 @ V_{IN} = 4.5 V, R1 = 20 kΩ

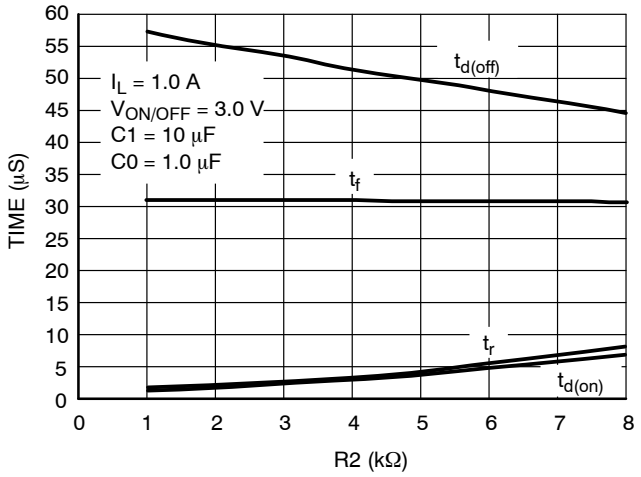


Figure 8. Switching Variation R2 @ V_{IN} = 4.5 V, R1 = 20 kΩ

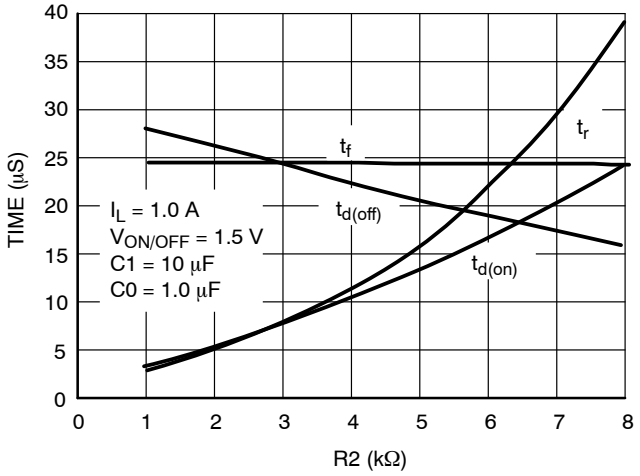


Figure 9. Switching Variation R2 @ V_{IN} = 2.5 V, R1 = 20 kΩ

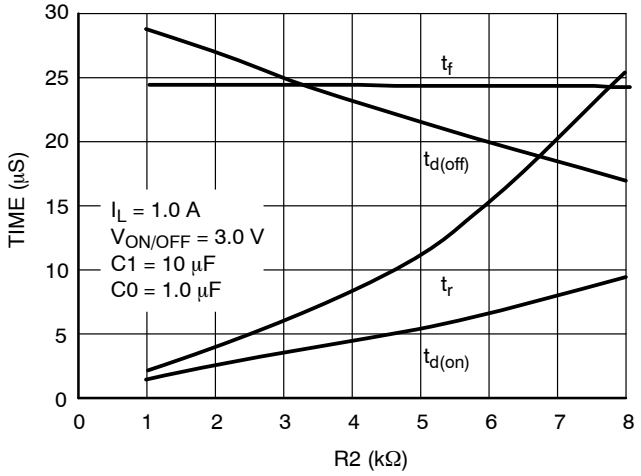


Figure 10. Switching Variation R2 @ V_{IN} = 2.5 V, R1 = 20 kΩ

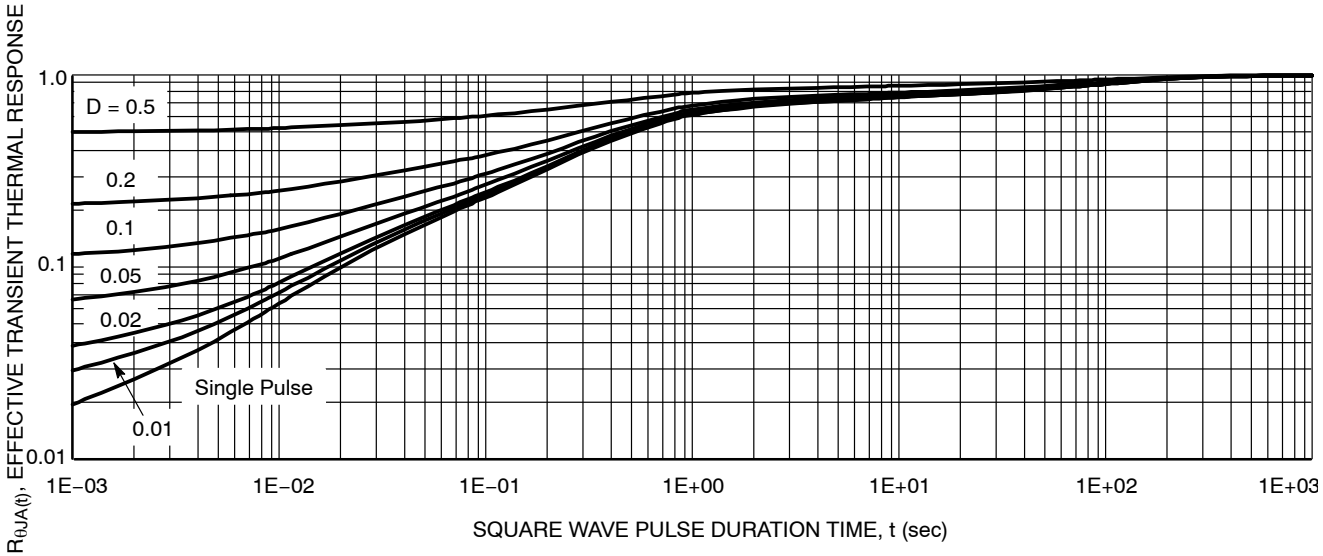
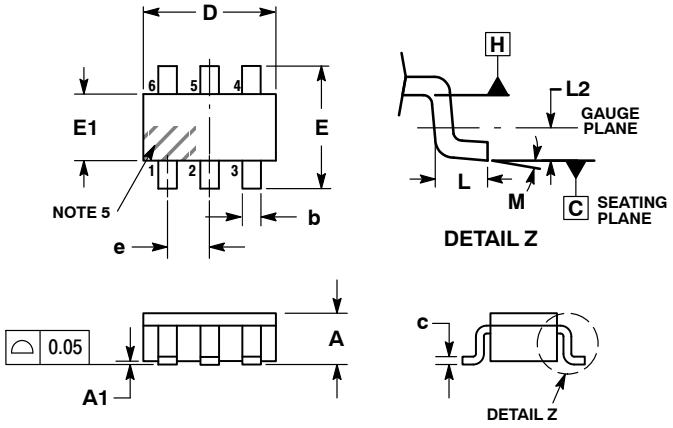


Figure 11. FET Thermal Response Normalized to $R_{\theta JA}$ at Steady State (1 inch Pad)

PACKAGE DIMENSIONS

TSOP−6
CASE 318G−02
ISSUE U

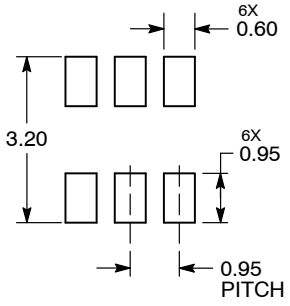


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	–	10°

STYLE 11:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1/GATE 2

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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